

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



HC4D30120D



TO247-3L

Maximum Ratings (T_c=25°C unless otherwise specified)

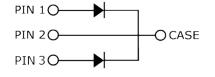
HC4D30120D

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	٧		
V_R	DC Peak Reverse Voltage	1200	V		
$\boldsymbol{I}_{_{\boldsymbol{F}}}$	Continuous Forward Current (Per Leg/Device)	44/88 21.5/43 15/30	А	T _c =25°C T _c =135°C T _c =152°C	Fig. 3
$\boldsymbol{I}_{\text{FRM}}$	Repetitive Peak Forward Surge Current	T _C =25°C		T_c =25°C, t_p =10 ms, Half Sine Pulse T_c =110°C, t_p =10 ms, Half Sine Pulse	
\mathbf{I}_{FSM}	Non-Repetitive Forward Surge Current	100* 85*	А	T_c =25°C, t_p =10 ms, Half Sine Pulse T_c =110°C, t_p =10 ms, Half Sine Pulse	Fig. 8
$\mathbf{I}_{\mathrm{F,Max}}$	Non-Repetitive Peak Forward Current	900* 750*	А	T_c =25°C, t_p =10 μ s, Pulse T_c =110°C, t_p =10 μ s, Pulse	Fig. 8
P _{tot}	Power Dissipation (Per Leg/Device)	220/440 95/190	W	T _c =25°C T _c =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-960V	
∫i²dt	i²t value	50* 36*	A²s	$T_c = 25^{\circ}C$, $t_p = 10 \text{ ms}$ $T_c = 110^{\circ}C$, $t_p = 10 \text{ ms}$	
T	Operating Junction Range	-55 to +175	°C		
T _{stg}	Storage Temperature Range	-55 to +135	°c		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

^{*} Per Leg, ** Per Device









Electrical Characteristics (Per Leg)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.6 2.3	1.8 3	V	I _F = 15 A T _J =25°C I _F = 15 A T _J =175°C	Fig. 1
I_R	Reverse Current	35 120	200 μA $V_R = 1200 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 1200 \text{ V } T_J = 175^{\circ}\text{C}$		$V_R = 1200 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 1200 \text{ V } T_J = 175^{\circ}\text{C}$	Fig. 2
Q _c	Total Capacitive Charge	77.5		nC	$V_R = 800 \text{ V, } I_F = 15\text{A} \\ di/dt = 200 \text{ A/}\mu\text{s} \\ T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	1200 70 50		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 800 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	Fig. 6
E _c	Capacitance Stored Energy	22.1		μJ	V _R = 800 V	Fig. 7

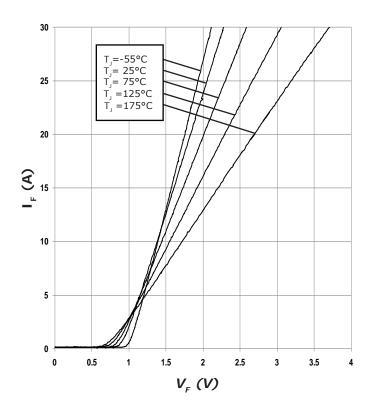
Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
$R_{_{\theta JC}}$	Thermal Resistance from Junction to Case	0.34** 0.68*	°C/W	Fig. 9

^{**} Per Device, * Per Leg

Typical Performance (Per Leg)





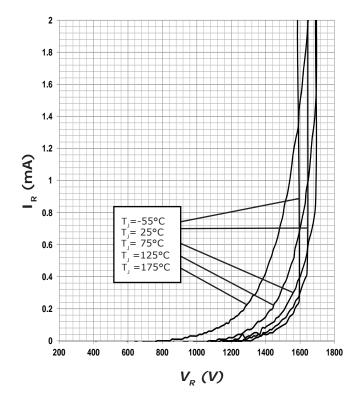
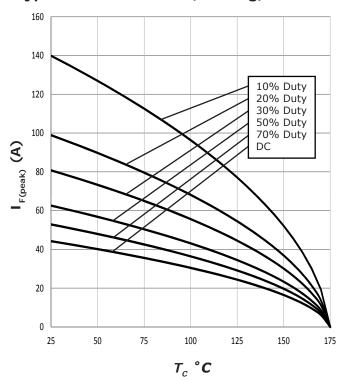


Figure 2. Reverse Characteristics



Typical Performance (Per Leg)



 T_c °C

Figure 3. Current Derating

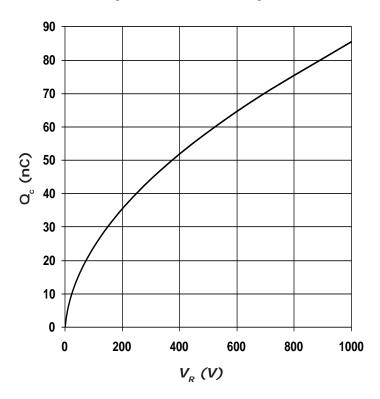


Figure 5. Recovery Charge vs. Reverse Voltage

Figure 4. Power Derating

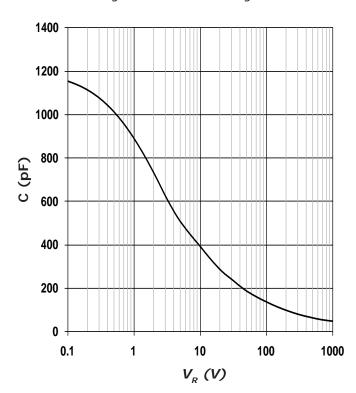
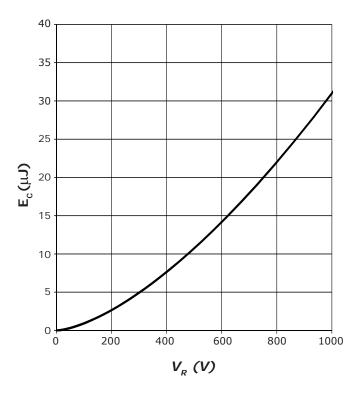


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance



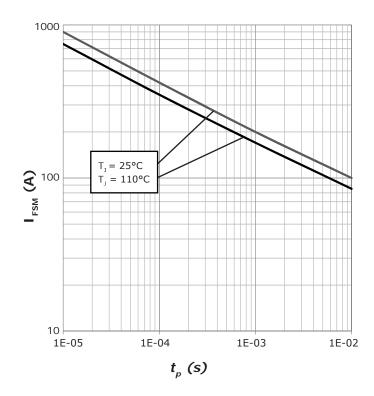


Figure 7. Typical Capacitance Stored Energy, per leg

Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform), per leg

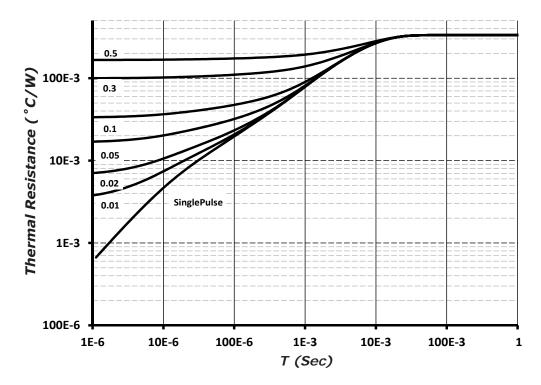
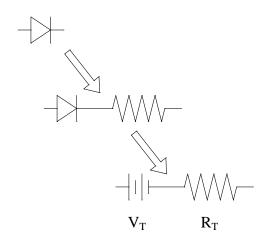


Figure 9. Device Transient Thermal Impedance

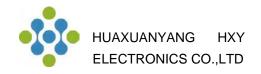
Diode Model



$$Vf_T = V_T + If * R_T$$

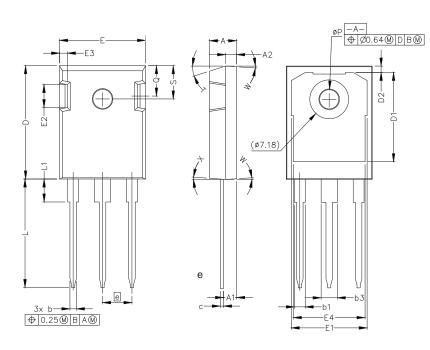
 $V_T = 0.97 + (T_j * -2.12*10^{-3})$
 $R_T = 0.031 + (T_j * 3.92*10^{-4})$

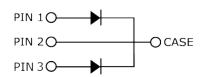
Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C



Package Dimensions

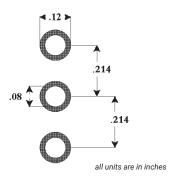
Package TO247-3L





DOS	Inc	hes	Millimeters		
POS	Min	Max	Min	Max	
А	.190	.205	4.83	5.21	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b3	.113	.133	2.87	3.38	
С	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
E	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
N		(3		
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	17.5° REF				
W	3.5° REF				
Х	4° REF				

Recommended Solder Pad Layout



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